

MITSUBISHI LASER DIODES

# ML9XX6 SERIES

InGaAsP - MQW - FP LASER DIODES

**TYPE  
NAME**

**ML920J6S , ML920K6S  
ML925B6F , ML925C6F**

## DESCRIPTION

ML9XX6 series are InGaAsP laser diodes which provides a stable, single transverse mode oscillation with emission wavelength of 1550nm and standard continuous light output of 5mW.

ML9XX6 are hermetically sealed devices having the photodiode for optical output monitoring. This high performance, high reliability, and long-life laser diode is suitable for such applications as the light sources for long distance optical communication systems.

## FEATURES

- 1550nm typical emission wavelength, FP-LDs
- Low threshold current, low operating current
- Wide temperature range operation  
(T<sub>c</sub>=-40 to +85°C)
- High reliability, long operation life
- Have a lens-cap (ML925C6F, ML920K6S)
- MQW\* active layer  
\* Multiple Quantum Well

## APPLICATION

Optical communication system

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings[Note 1]	Unit
P <sub>o</sub>	Light output power	CW	6[4]	mW
V <sub>RL</sub>	Reverse voltage (laser diode)	-	2	V
V <sub>RD</sub>	Reverse voltage (Photodiode)	-	20	V
I <sub>FD</sub>	Forward current (Photodiode)	-	2	mA
T <sub>c</sub>	Case temperature	-	-40 ~ +85	°C
T <sub>stg</sub>	Storage temperature	-	-40 ~ +100	°C

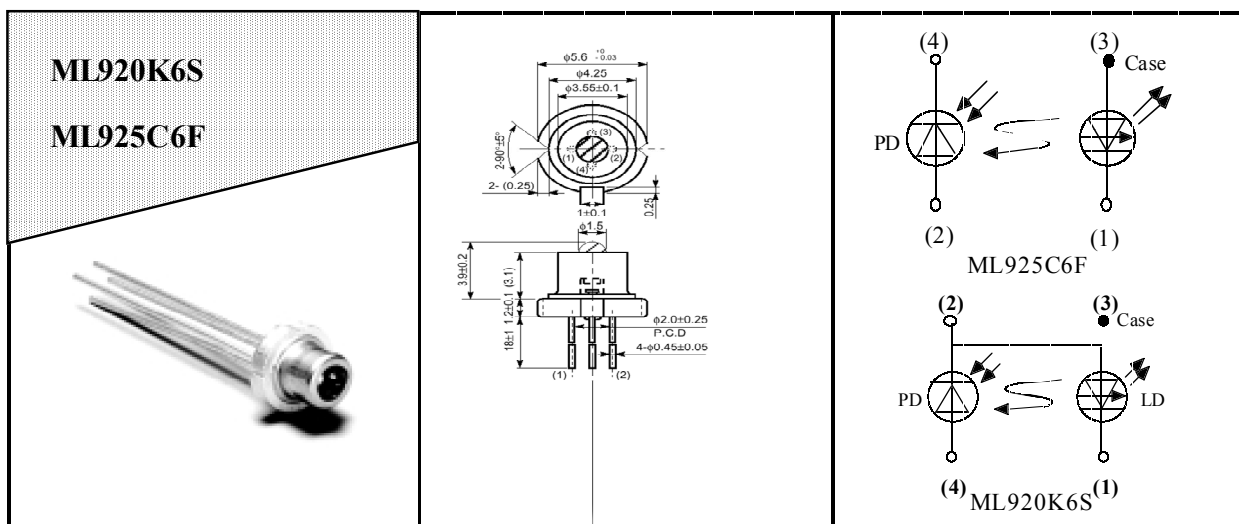
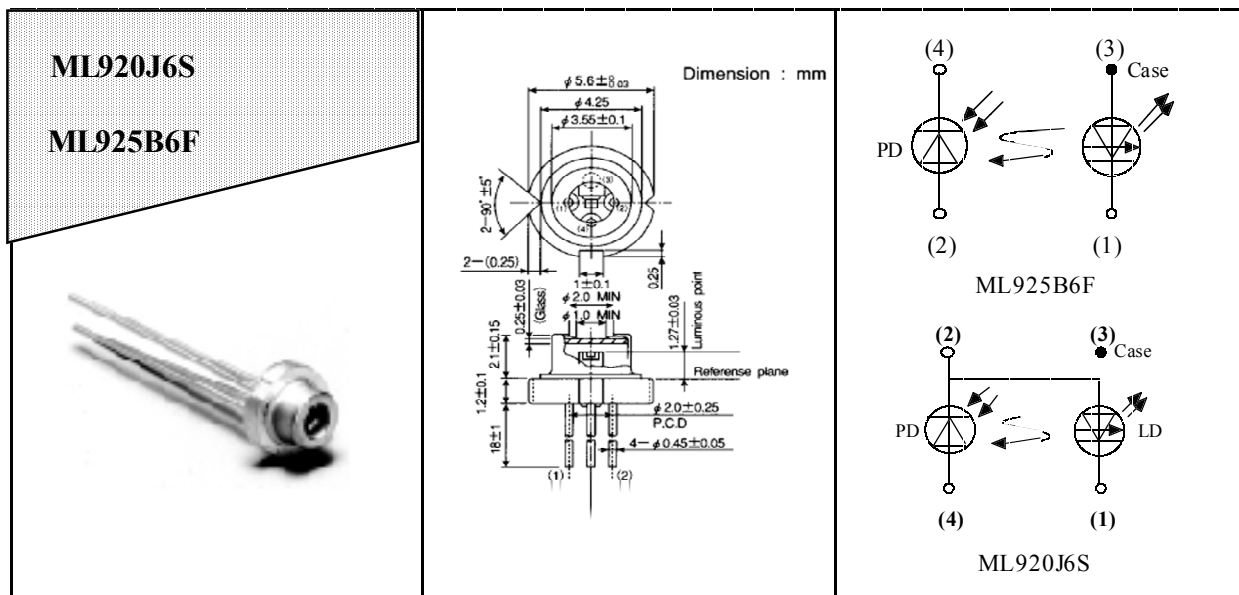
## ELECTRICAL/OPTICAL CHARACTERISTICS (T<sub>c</sub>=25°C) [Note 1]

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I <sub>th</sub>	Threshold current	CW	-	10	30	mA
I <sub>op</sub>	Operating current	CW, P <sub>o</sub> =5mW[3mW]	-	30	50	mA
V <sub>op</sub>	Operating voltage	CW, P <sub>o</sub> =5mW[3mW]	-	1.1	1.5	V
η	Slope efficiency	CW, P <sub>o</sub> =5mW[3mW]	0.15[0.1]	0.25[0.2]	-	mW/mA
λ <sub>p</sub>	Peak wavelength	CW, P <sub>o</sub> =5mW[3mW]	1520	1550	1580	nm
Δλ	Spectral width (RMS)	CW, P <sub>o</sub> =5mW[3mW]	-	1.5	3	nm
θ <sub>∥</sub>	Beam divergence angle (parallel)	CW, P <sub>o</sub> =5mW[3mW]	-	25[11]	-	deg.
θ <sub>⊥</sub>	Beam divergence angle (perpendicular)	CW, P <sub>o</sub> =5mW[3mW]	-	30[11]	-	deg.
t <sub>r</sub> , t <sub>f</sub>	Rise and Fall time	If=I <sub>th</sub> , P <sub>o</sub> =5mW[3mW], 10 - 90%	-	0.3	0.7	ns
I <sub>m</sub>	Monitoring output current	CW, P <sub>o</sub> =5mW[3mW], V <sub>RD</sub> =1V	0.1	0.5	-	mA
I <sub>D</sub>	Dark current (Photodiode)	V <sub>RD</sub> =10V	-	0.01	0.1	μA
C <sub>t</sub>	Capacitance (Photodiode)	V <sub>RD</sub> =10V, f=1MHz	-	10	20	pF

Note 1 : [ ] applied to the lens cap type

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**InGaAsP-MQW-FP-LASER DIODES**

**OUTLINE DRAWINGS**



## TYPICAL CHARACTERISTICS

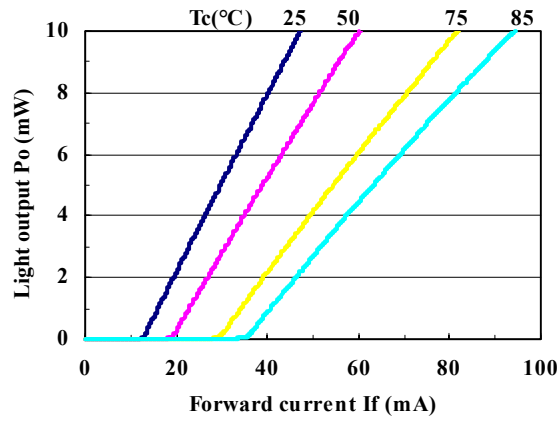


Fig.1 Light output vs. forward current

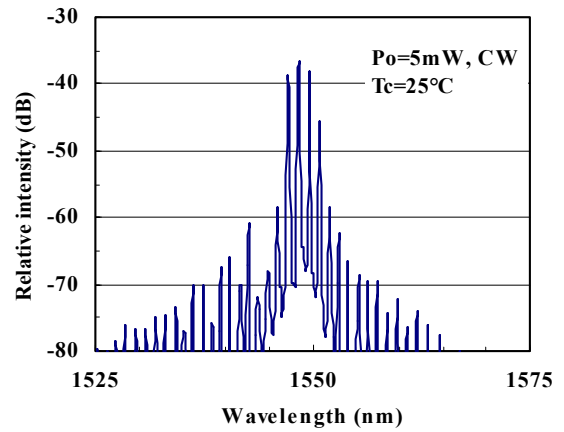


Fig.2 Spectrum

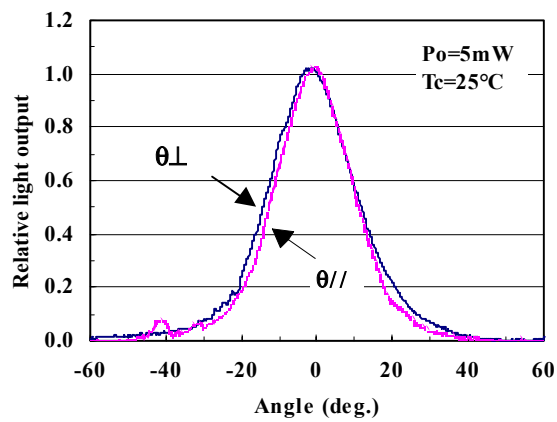


Fig.3 Far field patterns